

7. (Amended) A semiconductor device according to claim 1, wherein the base metal is Ni, Cu or Cr.

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8. (Amended) A semiconductor device according to claim 2, wherein the base metal is Ni,

Cu or Cr.

9. (Amended) A semiconductor device according to claim 3, wherein the base metal is Ni,

Cu or Cr.

16. (Twice Amended) A semiconductor device comprising a capacitor including a first electrode of a metal, a ferroelectric film formed above the first electrode, and a second electrode of a metal formed above the ferroelectric film; at least one of the first electrode and the second electrode being an electrode of a base metal, and a transistor connected to the first electrode or the second electrode, further comprising

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an intermediate layer of perovskite crystal structure formed between the electrode of the base metal and the ferroelectric film, materials of the intermediate layer being different from materials of the first electrode, the second electrode and the ferroelectric film.
